



Pin Assignments

Vcc(A)[1]

GND 2

A 3

(Top View)

SOT26 SOT363 SOT563

(Bottom View)

Vcc(A) 1 • 6 Vcc(B)

X2-DFN1409-6 **Chip Scale** Alternative

• 4 B

● 5 DIR

A 3

GND 2

Applications

6 Vcc(B)

15 DIR

14 B

(Top View)

Vcc(A) [1] [6] Vcc(B)

GND 2 5 DIR

A 3 [4 B

X2-DFN1410-6

(Top View)

Vcc(A) [1] [6] Vcc(B)

GND 2 5 DIR

A 3 [4 B

X2-DFN1010-6

SINGLE BIT DUAL POWER SUPPLY TRANSLATING **TRANSCEIVER WITH 3 STATE OUTPUTS**

Description

The 74LVC1T45 is a single bit, dual supply transceiver with 3-state outputs suitable for transmitting a single logic bit across different voltage domains. The A input/output pin is designed to track V_{CCA} while the B input/output tracks V_{CCB}. This arrangement allows for universal low-voltage translation between any voltages from 1.65V to 5.5V. The Direction pin (DIR) controls the direction of the transceiver and in a logic voltage related to V_{CCA}. When a high logic level is applied to DIR the A pin becomes an input and the B pin becomes the output. Conversely, the roles of A and B are reversed when DIR is asserted low.

The 3-state feature occurs when either of the power supply voltages are zero. This is also an loff feature and allows for the output to remain in a high impedance state with both power supplies at 0V, preventing and damaging backflow currents and providing power down electrical isolation up to 5.5V as not to interfere with any logic activity on pin A or B.

Features

- Wide Supply Voltage Range:
 - V_{CC}(A): from 1.65V to 5.5V
 - V_{CC}(B): from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption 16µA Maximum I_{CC}
- High Noise Immunity (100mV Hysteresis Typical)
- IOFF Supports Partial-Power-Down Mode Operation
- IOFF Controlled by Either VCC Being at 0 V
- Inputs Accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-up Exceeds 100mA per JESD 78, Class I
- X2-DFN1409-6 Package Designed as a Direct Replacement for Chip Scale Packaging.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Click for Ordering Information

Document number: DS35804 Rev. 3 - 2

October 2014 © Diodes Incorporated

- Well suited to join logic types operating at different voltages Power Down Signal Isolation If either voltage domain is turned off the signal is isolated and
- Wide array of products such as:

Voltage Level Translation

Cell Phones, Tablets, E-Readers

there is no loading on signal lines

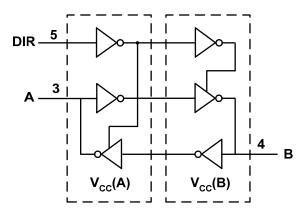
- PCs, Notebooks, Netbooks, Ultrabooks
- Networking, Routers, Gateways
- Computer Peripherals, Hard Drives, CD/DVD ROM
- TV, DVD, DVR, Set-Top Box
- Personal Navigation / GPS
- MP3 Players, Cameras, Video Recorders



Pin Descriptions

Pin Name	Pin	Function
VCC(A)	1	Supply for I/O pin A and reference for DIR
GND	2	Ground
A	3	Data Input/Output
В	4	Data Input/Output
DIR	5	Direction Control
VCC(B)	6	Supply for I/O pin B

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation
L	B data to A output
Н	A data to B output

	Inputs		Outp	outs
Α	В	Α	В	
*	L	L	L	*
*	Н	L	Н	*
L	*	Н	*	L
Н	*	Н	*	Н

*Pin condition not applicable as defined by DIR.

Symbol	Parameter		Rating	Unit
ESD HBM	Human Body Model ESD Protection		2	KV
ESD CDM	Charged Device Model ESD Protection		1	KV
ESD MM	Machine Model ESD Protection		200	V
V _{CC} (A), V _{CC} (B)	Supply Voltage Range		-0.5 to +6.5	V
VI	Input Voltage Range		-0.5 to +6.5	V
Vo	Voltage Applied to Output in High Impedance or IOFF	State	-0.5 to +6.5	V
	Voltage Applied to Output in Lligh or Low State	A pin	-0.3 to V _{CC} (A) +0.5	V
Vo	Voltage Applied to Output in High or Low State	B pin	-0.3 to V _{CC} (B) +0.5	V
l _{IK}	Input Clamp Current VI<0	·	-50	mA
Ι _{ΟΚ}	Output Clamp Current		-50	mA
lo	Continuous Output Current		±50	mA
	Continuous Current Through V _{cc} or GND		±100	mA
TJ	Operating Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature		-65 to +150	°C

Absolute Maximum Ratings (Note 4) (@T_A = +25°C, unless otherwise specified.)

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Param	eter	V _{CC} Inputs	V _{CC} Outputs	Min	Max	Units
V _{CC} (A)			-	-	1.65	5.5	V
V _{CC} (B)	Operating V	oltage	-	-	1.65	5.5	V
	High-Level I	nput	V _{CC} = 1.65V to 1.95V	-	0.65 X V _{CC(A)}	_	
.,	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	1.7	_	.,
VIH	Referenced	to	V _{CC} = 3V to 3.6V	-	2	_	V
	V _{CC} (A)		V _{CC} = 4.5V to 5.5V	-	0.7 X V _{CC(A)}	-	
	Low-Level Ir	nout	V _{CC} = 1.65V to 1.95V	-	_	0.35 X V _{CC(A)}	
	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	_	0.7	
VIL	Referenced		V _{CC} = 3V to 3.6V	-	_	0.8	V
	V _{CC} (A)		V _{CC} = 4.5V to 5.5V	-	_	0.3 X V _{CC(A)}	
	High-Level I	nput	V _{CC} = 1.65V to 1.95V	-	0.65 X V _{CC(B)}	-	
.,	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	1.7	_	
VIH	Referenced		V _{CC} = 3V to 3.6V	-	2	-	V
	V _{CC} (B)		V _{CC} = 4.5V to 5.5V	-	0.7 X V _{CC(B)}	-	
	Low-Level Ir	nout	V _{CC} = 1.65V to 1.95V	-	-	0.35 X V _{CC(B)}	
.,	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	_	0.7	
VIL	Referenced		V _{CC} = 3V to 3.6V	-	_	0.8	V
	V _{CC} (B)		V _{CC} = 4.5V to 5.5V	-	_	0.3 X V _{CC(B)}	
VI	Input Voltag	е	-	-	0	5.5	V
Vo	Output Volta	ige	-	-	0	Vcc	V
			-	V _{CC} = 1.65V to 1.95V	_	-4	
		_	-	V _{CC} = 2.3V to 2.7V	_	-8	
Іон	High-Level (Dutput	-	V _{CC} = 3V to 3.6V	_	-16	mA
	Current		-	V _{CC} = 4.5V to 5.5V	_	-24	
			-	V _{CC} = 1.65V to 1.95V	_	-32	
			_	V _{CC} = 2.3V to 2.7V	_	4	
			-	V _{CC} = 3V to 3.6V	_	8	
IOL	Low-Level C	Output	-	V _{CC} = 4.5V to 5.5V	_	16	mA
	Current		-	V _{CC} = 1.65V to 1.95V	_	24	
			-	V _{CC} = 2.3V to 2.7V	_	32	
			V _{CC} = 1.65V to 1.95V	-	_	20	
	Input	Data	V _{CC} = 2.3V to 2.7V	-	_	20	
	Transition	Inputs	V _{CC} = 3V to 3.6V	-	-	10	A /
Δt/ΔV	Rise or Fall		V _{CC} = 4.5V to 5.5V	-	-	5	ns/V
	Rate	Control Inputs	V _{CC} = 1.65V to 5.5V	-	_	5	
TA	Operating Fi		-	-	-40	+125	°C

Note: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (@T_A = +40°C to +85°C, unless otherwise specified.)

• • • • •		_	0		X (5)	Т	A = +25°	°C	T _A = -40°C	to +85°C	
Symbol	Parameter	Test	Conditions	V _{CC} (A)	V _{CC} (B)	Min	Тур	Max	Min	Max	Unit
		I _{OH} = -100	AL	1.65V to 5.5V	1.65V to 5.5V	I	-	-	V _{CC} -0.1	=	
		I _{OH} = -4mA	4	1.65V	1.65V	I	-	-	1.2	=	
Voh	High Level	I _{OH} = -8mA	۱.	2.3V	2.3V	_	-	-	1.9	-	V
	Output Voltage	I _{OH} = -24m	A	3V	3V	-	-	-	2.4	-	
		I _{OH} = -32m	A	4.5V	4.5V	-	-	-	3.8	-	
		I _{OL} = 100μ	A	1.65V to 5.5V	1.65V to 5.5V	1	-	-	_	0.1	
		I _{OL} = 4mA		1.65V	1.65V	I	-	-	-	0.45	
Vol	Low-Level Output Voltage	I _{OL} = 8mA		2.3V	2.3V	1	-	-	-	0.3	V
	vollage	I _{OL} = 24mA		3V	3V	1	-	-	-	0.55	
		I _{OL} = 32mA		4.5V	4.5V	1	-	-	-	0.55	
lı	Input Current	DIR	V _I = V _{CC} (A) or GND	0 to 5.5V	0 to 5.5V	_	-	± 1	-	± 2	μA
IOFF	Power Down	A Pin V_1 or $V_0 = 0$ to		0	0V to 5.5V	_	-	± 1	-	± 2	μA
	Leakage Current	B Pin 5.5V		0 to 5.5V	0	-	-	± 1	-	± 2	
1	3-State Leakage	A Pin $V_O = V_{CC}(A)$		1.65V to 5.5V	1.65V to 5.5V	-	-	± 1	-	± 2	μA
I _{OZ}	Current	B Pin $V_0 = V_{CC}(B)$		1.65V to 5.5V	1.65V to 5.5V	-	-	± 1	-	± 2	μΑ
			V _I = 5.5V or GND		1.65V to 5.5V	I	-	-	-	3	
I _{CCA}	Supply Current	$V_{\rm I} = 5.5 V C$ $I_{\rm O} = 0$	I GND	5.5V	0	_	-	-	-	2	μA
		10 - 0		0	5.5V	-	-	-	-	-2	
		VI = 5.5V c		1.65V to 5.5V	1.65V to 5.5V	-	-	-	-	3	
I _{CCB}	Supply Current	$I_0 = 0$		0V	5.5V	_	-	-	-	2	μA
		.0 0		5.5V	0V	_	-	-	-	-2	
I _{CCA} + I _{CCB}	Supply Current	V _I = 5.5V c	or GND I _O = 0	1.65V to 5.5V	1.65V to 5.5V	-	_	_	_	4	μA
ΔI _{CCA}	Additional Supply	A pin I	$A = V_{CC}(A) - 0.6V$ DIR = V _{CC} (A) B = open	3V to 5.5V	3V to 5.5V	_	_	_	_	50	μA
	Current	DIR $V_{CC}(A) - 0.6V$ DIR $A = V_{CC}(A)$ or GND B = open								50	p, r
ΔI _{CCB}	Additional Supply Current	$B = V_{CC}(B) - 0.6V$ $B pin \qquad DIR = GND$ $A = open$		3V to 5.5V	3V to 5.5V	_	_	_	_	50	μA
CI	Input Capacitance		/ _I = V _{CC} (A) or GND	3.3V	3.3V	-	2.5	-	-	_	pF
C _{IO}	Input/Output Capacitance		/ _I = V _{CC} (A)/(B) or GND	3.3V	3.3V	_	6.0	-	_	-	pF



Electrical Characteristics (@T_A = +40°C to +125°C, unless otherwise specified.)

0	Demonstern	.	4 O	X (A)	V (D)	T _A = -40°C	to +125°C	1114
Symbol	Parameter	Tes	t Conditions	V _{CC} (A)	V _{CC} (B)	Min	Max	Unit
		I _{OH} = -100µ.	4	1.65V to 5.5V	1.65V to 5.5V	V _{CC} – 0.1	-	
	High Level	I _{OH} = -4mA		1.65V	1.65V	1.2	-	
Voh	Output	I _{OH} = -8mA		2.3V	2.3V	1.9	-	V
	Voltage	I _{OH} = -24mA		3V	3V	2.4	-	
		I _{OH} = -32mA		4.5V	4.5V	3.8	-	
		l _{OL} = 100μΑ		1.65V to 5.5V	1.65V to 5.5V	_	0.1	
		I _{OL} = 4mA		1.65V	1.65V	_	0.45	
Vol	High-Level	I _{OL} = 8mA		2.3V	2.3V	_	0.3	V
	Input Voltage	I _{OL} = 24mA		3V	3V	_	0.55	
		I _{OL} = 32mA		4.5V	4.5V	_	0.55	
lj	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	0 to 5.5V	0 to 5.5V	_	± 2	μA
IOFF	Power Down Leakage	A Pin	$V_1 \text{ or } V_0 = 0 \text{ to } 5.5 \text{V}$	0	1.65V to 5.5V	_	± 2	μΑ
IOFF	Current	B Pin		1.65V to 5.5V	0V	_	± 2	μ.
I _{OZ}	3-State Leakage	B Pin V _O =V _{CC} (B) DIR = 0 V	-V ₁ = 0 to 5.5V	1.65V to 5.5V	1.65V to 5.5V	_	±2	- μΑ
102	Current	A Pin $V_0 = V_{CC}(A)$ DIR= $V_{cc}(A)$		1.65V to 5.5V	1.65V to 5.5V	_	±2	
	Supply	V _I = 5.5V or	CND	1.65V to 5.5V	1.65V to 5.5V	_	3	
I _{CCA}	Current	$V_{\rm I} = 0.5 V 0 I$	OND	5.5V	0	_	2	μA
	Guilein	10 - 0		0	5.5V	-	-2	
	Cumply	V _I = 5.5V or	CND	1.65V to 5.5V	1.65V to 5.5V	-	3	
I _{CCB}	Supply Current	$V_{\rm I} = 0$	GND	5.5V	0	_	2	μA
	Current	10 - 0		0	5.5V	_	-2	
ICCA + ICCB	Supply Current	V _I = 5.5V or I _O = 0	GND	1.65V to 5.5V	1.65V to 5.5V	_	4	μA
	Additional	A pin $A = V_{CC} (A) - 0.6V$ DIR = V _{CC} (A) B = open		3V to 5.5V	2)/ to 5 5)/		50	
ΔI _{CCA}	Supply Current	DIR A= \	DIR= V _{CC} (A) -0.6V		3V to 5.5V	_	50	μA
ΔI _{CCB}	Additional Supply Current	B pin DIR	V _{CC} (B) -0.6V = GND open	3V to 5.5V	3V to 5.5V	_	50	μA



Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
		SOT26		-	166	-	
		SOT363		-	371	-	
0	Thermal Resistance Junction-	SOT563	Noto 6	-	290	-	°C/W
θ_{JA}	UJA to-Ambient	DFN1410	Note 6	-	430	-	
		DFN1409		-	450	-	
		DFN1010		-	510	-	
		SOT26		-	46	-	
		SOT363		-	143	-	
0	Thermal Resistance Junction-	SOT563	Nata C	-	96	-	°C/W
θ_{JC}	to-Case	DFN1410	Note 6	-	190	-	C/W
	DFN1409		-	200	-		
		DFN1010		-	250	-	

Package Characteristics (V_{CC} = 3.3V, T_A = +25°C, unless otherwise specified.)

6. Test condition for SOT26, SOT363, DFN1410, DFN1409 and DFN1010 : Device mounted on FR-4 substrate PC board, 2oz copper with minimum Note: recommended pad layout.

Parameter	From (Input)	To (Output)		e 1.8V 15V		= 2.5V .2V		= 3.3V .3V		3)= 5V).5V	Unit
	(input)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	3	17.7	2.2	10.3	1.7	8.3	1.4	7.5	ns
t _{pHL}		Б	2.8	14.3	2.2	8.5	1.8	8.1	1.7	7.5	ns
t _{pLH}	в	А	3	17.7	2.3	16	2.1	15.5	1.9	15.1	
t _{pHL}		A	2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	ns
t _{pHZ}	DID	•	5.2	19.4	4.8	18.5	4.7	18.4	5.1	17.1	
t _{pLZ}	DIR	A	2.3	10.5	2.1	10.5	2.4	10.7	3.1	10.9	ns
t _{pHZ}	DID	В	6.4	21.9	4.9	11.5	4.6	10.3	2.8	8.2	
t _{pLZ}	DIR	В	4.2	17	3.7	9.6	3.3	8.8	2.4	8.0	ns
t _{pZH}	DID	•	-	33.7	-	25.2	-	23.9	-	21.5	
t _{pZL}	DIR	A	-	36.2	-	24.4	-	22.9	-	20.4	ns
t _{pZH}	DID	В	-	28.2	-	20.8	-	19	-	18.1	
t _{pZL}	DIR	В	_	33.7	-	27	-	25.5	-	24.1	ns

Switching Characteristics (cont.) (V_{CC} (A) = 2.5V ± 0.2V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V		8) = 5V 9.5V	Unit
	(input)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	20
t _{pHL}	~	Б	2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	ns
t _{pLH}	в	А	2.2	10.3	1.5	8.5	1.4	8	1	7.5	
t _{pHL}	В	A	2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	ns
t _{pHZ}	DIR	А	3	8.1	3.1	8.1	2.8	8.1	3.2	8.1	
t _{pLZ}	DIR	A	1.3	5.9	1.3	5.9	1.3	5.9	1	5.8	ns
t _{pHZ}	DIR	В	5.5	23.7	3.6	11.4	3.5	10.2	2.4	7.1	
t _{pLZ}	DIR	В	3.9	18.9	3.2	9.6	2.8	8.4	1.8	5.3	ns
t _{pZH}	DID		-	29.2	-	18.1	-	16.4	-	12.8	
t _{pZL}		IR A	-	32.2	_	18.9	-	17.2	_	13.3	ns
t _{pZH}	DIR	В	-	21.9	_	14.4	-	12.3	-	10.9	ns



Parameter	From	To (Output)) = 1.8V 15V		= 2.5V .2V		= 3.3V .3V		3) = 5V).5V	Unit
	(Input)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	А	В	2.1	15.5	1.4	8	0.7	5.8	0.7	4.4	ns
t _{pHL}	A	Б	2	12.6	1.3	7	0.8	5	0.7	4	115
t _{pLH}	в	А	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	20
t _{pHL}		A	1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	ns
t _{pHZ}	DIR	^	2.9	7.3	3	7.3	2.8	7.3	3.4	7.3	-
t _{pLZ}	DIR	A	1.8	5.6	1.6	5.6	2.2	5.7	2.2	5.7	ns
t _{pHZ}	DIR	В	4.0	20.5	3.5	10.1	2.9	8.8	2.4	6.8	
t _{pLZ}		В	3.3	14.5	2.9	7.8	2.4	7.1	1.7	4.9	ns
t _{pZH}	DIR	•	-	22.8	-	14.2	-	12.9	-	10.3	-
t _{pZL}		A	-	27.6	-	15.5	-	13.8	-	11.3	ns
t _{pZH}	DIR	В	-	21.1	-	13.6	-	11.5	-	10.1	20
t _{pZL}		В	_	19.9	_	14.3	_	12.3	-	11.3	ns

Switching Characteristics (cont.) (V_{CC} (A) = 3.3V ± 0.3V, T_A = -40°C to +85°C, see Figure 1)

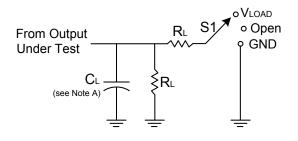
Switching Characteristics (cont.) (V_{CC} (A) = 5V \pm 0.5V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V		3)= 5V .5V	Unit
	(input)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max]
t _{pLH}	A	В	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t _{pHL}	~	В	1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	115
t _{pLH}	в	А	1.4	8.5	1	5.1	0.7	4.4	0.5	3.9	
t _{pHL}	В	A	1.7	8.5	0.9	4.6	0.7	4	0.5	3.5	ns
t _{pHZ}	DIR	А	2.1	5.4	2.2	5.4	2.2	5.5	2.2	5.4	
t _{pLZ}	DIK	A	0.9	3.8	1	3.8	1	3.7	0.9	3.7	ns
t _{pHZ}	DIR	В	4.8	20.2	2.5	9.8	1	8.5	2.2	6.5	
t _{pLZ}		В	4.2	14.8	2.5	7.4	2.5	7	1.6	4.5	ns
t _{pZH}	DID	•	-	22	-	12.5	-	11.4	-	8.4	
t _{pZL}		DIR A	_	27.2	_	14.4	_	12.5	-	10	ns
t _{pZH}	DIR	В	_	18.9	_	11.3	_	9.1	_	7.6	ns

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

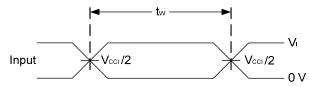
Power Dis	Parameter sipation Capacitance	Test Conditions	V _{CC} (A) = V _{CC} (B) = 1.8V Typ	V _{CC} (A) = V _{CC} (B) = 2.5V Typ	V _{CC} (A) = V _{CC} (B) = 3.3V Typ	V _{CC} (A) = V _{CC} (B) = 5V Typ	Unit
	A- input, B- output	C _L = 0 pF	3	4	4	4	
C _{pd} (A)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	18	19	20	21	pF
	A- input, B- output	C _L = 0 pF	18	19	20	21	
C _{pd} (B)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	3	4	4	4	pF

Parameter Measurement Information

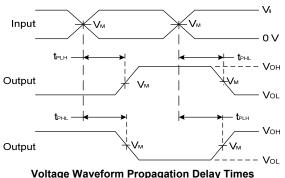


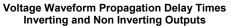
TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

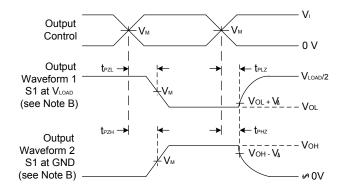
V	Inputs		N N	6			
V _{cc}	VI	t _r /t _f	V _M	V _{LOAD}	CL	RL	VΔ
1.8V±0.15V	V _{CCI}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
2.5V±0.2V	V _{CC}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V
5V±0.5V	V _{CC}	≤2.5ns	V _{CCO} /2	$2 \times V_{CCO}$	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration







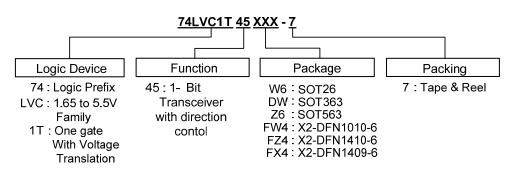
Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1 Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control.
 - Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
 - C. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{\mathsf{dis.}}$
 - E. t_{PZL} and t_{PZH} are the same as $t_{\text{EN.}}$
 - F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$
 - G. V_{CCI} is the V_{CC} associated with the input.
 - F. V_{CCO} is the V_{CC} associated with the output.



Ordering Information

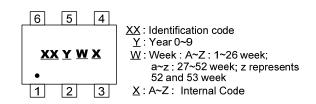


Part Number	Package Code	Deekening	7" Tape and Reel (Note 7)		
Fait Number	Fackage Code	Packaging	Quantity	Part Number Suffix	
74LVC1T45W6-7	W6	SOT26	3000/Tape & Reel	-7	
74LVC1T45DW-7	DW	SOT363	3000/Tape & Reel	-7	
74LVC1T45Z6-7	Z6	SOT563	4000/Tape & Reel	-7	
74LVC1T45FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7	
74LVC1T45FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7	
74LVC1T45FX4-7	FX4	X2-DFN1409-6	5000/Tape & Reel	-7	

Note: 8. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

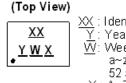
Marking Information

(1) SOT363, SOT563



Part Number	Package	Identification Code
74LVC1T45W6	SOT26	TT
74LVC1T45DW	SOT363	TR
74LVC1T45Z6	SOT563	TS

(2) X2-DFN1010-6, X2-DFN1410-6, and X2-DFN1409-6



XX : Identification Code Y : Year : 0~9

<u>Y</u>: Year : 0~9 <u>W</u>: Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week

 \underline{X} : A~Z : Internal code

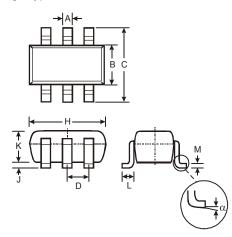
Part Number	Package	Identification Code
74LVC1T45FW4	X2-DFN1010-6	TR
74LVC1T45FX4	X2-DFN1409-6	TT
74LVC1T45FZ4	X2-DFN1410-6	TS



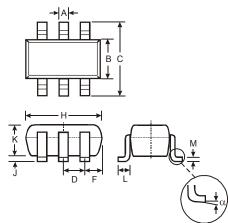
Package Outline Dimensions (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(1) Package Type: SOT26



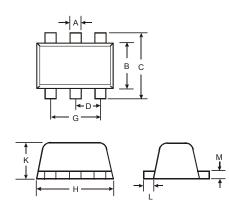
(2) Package Type: SOT363



SOT26								
Dim	Dim Min Max Typ							
Α	0.35	0.50	0.38					
в	1.50	1.70	1.60					
C	2.70	3.00	2.80					
D		_	0.95					
Н	2.90	3.10	3.00					
ب	0.013	0.10	0.05					
Κ	1.00	1.30	1.10					
_	0.35	0.55	0.40					
Μ	0.10	0.20	0.15					
α	0°	8°						
All D	imensi	ons in	mm					

	SOT363						
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
C	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
Н	1.80	2.20					
ر	0	0.10					
κ	0.90	1.00					
L	0.25	0.40					
М	0.10	0.22					
α	0°	8°					
All Di	mensions	in mm					

(3) Package Type: SOT563



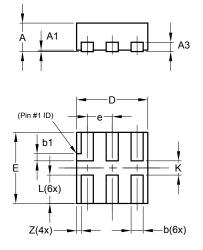
SOT563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
в	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Η	1.50	1.70	1.60			
κ	0.55	0.60	0.60			
L	0.10	0.30	0.20			
Μ	0.10	0.18	0.11			
All	Dimens	sions in	mm			



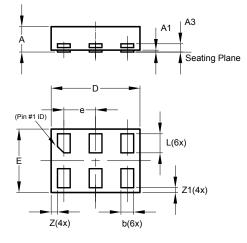
Package Outline Dimensions (cont.) (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(4) Package Type X2-DFN1010-6



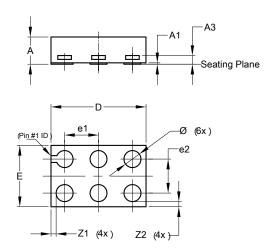
(5) Package Type: X2-DFN1410-6



X2-DFN1010-6							
Dim	Min	Max	Тур				
Α		0.40	0.39				
A1	0.00	0.05	0.02				
A3			0.13				
b	0.14	0.20	0.17				
b1	0.05	0.15	0.10				
D	0.95	1.05	1.00				
ш	0.95	1.05	1.00				
e			0.35				
L	0.35	0.45	0.40				
Κ	0.15						
Z			0.065				
All	Dimens	ions in	mm				

	X2-DFN1410-6							
Dim	Dim Min Max Typ							
Α		0.40	0.39					
A1	0.00	0.05	0.02					
A3			0.13					
b	0.15	0.25	0.20					
D	1.35	1.45	1.40					
Е	0.95	1.05	1.00					
е			0.50					
L	0.25	0.35	0.30					
Z	_	_	0.10					
Z1	0.045	0.105	0.075					
All	Dimens	ions in	mm					

(6) Package Type: X2-DFN1409-6 CHIP SCALE ALTERNATIVE



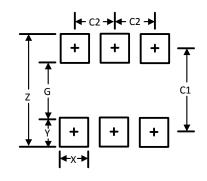
)	X2-DFN1409-6							
Dim	Dim Min Max							
Α	-	0.40	0.39					
A1	0	0.05	0.02					
A3	-	-	0.13					
Ø	0.20	0.30	0.25					
D	1.35	1.45	1.40					
Е	0.85	0.95	0.90					
e1	-	-	0.50					
e2	-	-	0.50					
Z1	-	-	0.075					
Z2	-	-	0.075					
All D	imens	ions in	mm					



Suggested Pad Layout

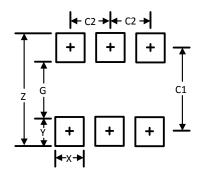
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package Type: SOT26

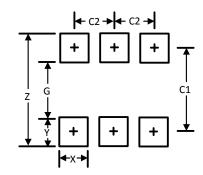


Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) Package Type: SOT363



(3) Package Type: SOT563



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

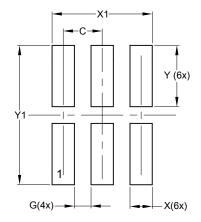
Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



Suggested Pad Layout (cont.)

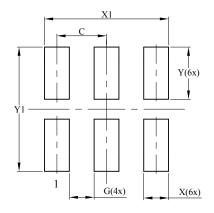
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(4) Package Type X2-DFN1010-6



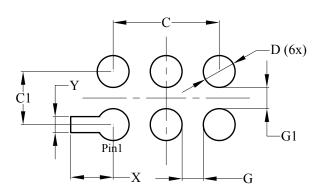
Dimensions	Value (in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

(5) Package Type: X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
х	0.250
X1	1.250
Y	0.525
Y1	1.250

(6) Package Type: X2-DFN1409-6



Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Y	0.150

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2014, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Buffers & Line Drivers category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

5962-9217601MSA 634810D 875140G HEF4022BP HEF4043BP NL17SG125DFT2G NL17SZ126P5T5G NLU1GT126CMUTCG NLU3G16AMX1TCG NLV27WZ125USG MC74HCT365ADTR2G BCM6306KMLG 54FCT240CTDB Le87401NQC Le87402MQC 028192B 042140C 051117G 070519XB 065312DB 091056E 098456D NL17SG07DFT2G NL17SG17DFT2G NL17SG34DFT2G NL17SZ07P5T5G NL17SZ125P5T5G NLU1GT126AMUTCG NLV27WZ16DFT2G 5962-8982101PA 5962-9052201PA 74LVC07ADR2G MC74VHC1G125DFT1G NL17SH17P5T5G NL17SZ125CMUTCG NLV17SZ07DFT2G NLV37WZ17USG NLVHCT244ADTR2G NC7WZ17FHX 74HCT126T14-13 NL17SH125P5T5G NLV14049UBDTR2G NLV37WZ07USG 74VHC541FT(BE) RHFAC244K1 74LVC1G17FW4-7 74LVC1G126FZ4-7 BCM6302KMLG 74LVC1G07FZ4-7 74LVC1G125FW4-7